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### Vishay Semiconductors

## **Insulated Ultrafast Rectifier Module, 230 A**



SOT-227	

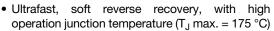
Package

PRIMARY CHARACTERISTICS						
V <sub>R</sub>	600 V					
I <sub>F(AV)</sub> per module at T <sub>C</sub> = 88 °C	230 A					
t <sub>rr</sub>	43 ns					
Type	Modules - diode FRFD Pt®					

SOT-227

#### **FEATURES**

- Two fully independent diodes
- Fully insulated package





- Low forward voltage drop
- Optimized for power conversion: welding and industrial SMPS applications
- · Easy to use and parallel
- · Industry standard outline
- UL approved file E78996



- · Designed and qualified for industrial level
- · Material categorization: for definitions of compliance please see www.vishav.com/doc?99912

#### **DESCRIPTION / APPLICATIONS**

The VS-UFB230FA60 insulated modules integrate two state of the art ultrafast recovery rectifiers in the compact, industry standard SOT-227 package. The diodes structure, and its life time control, provide an ultrasoft recovery current shape, together with the best overall performance, ruggedness and reliability characteristics.

These devices are thus intended for high frequency applications in which the switching energy is designed not to be predominant portion of the total energy, such as in the output rectification stage of welding machines, SMPS, DC/DC converters. Their extremely optimized stored charge and low recovery current reduce both over dissipation in the switching elements (and snubbers) and EMI/RFI.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS		
Cathode to anode voltage	$V_R$		600	V		
Continuous forward current per diode	I <sub>F</sub>	T <sub>C</sub> = 85 °C	141			
Single pulse forward current per diode	I <sub>FSM</sub>	T <sub>C</sub> = 25 °C	1400	Α		
Maximum power dissipation per module	$P_{D}$	T <sub>C</sub> = 85 °C	416	W		
RMS isolation voltage	V <sub>ISOL</sub>	Any terminal to case, t = 1 min	2500	V		
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +175	°C		

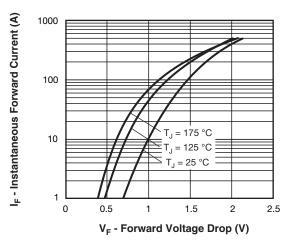


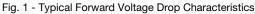
<b>ELECTRICAL SPECIFICATIONS PER DIODE</b> (T <sub>J</sub> = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage		I <sub>R</sub> = 100 μA	600	-	-	
		I <sub>F</sub> = 100 A	-	1.46	1.78	
Forward voltage	\ \ <u>\</u>	I <sub>F</sub> = 100 A, T <sub>J</sub> = 125 °C	-	1.23	1.52	V
Forward voltage	V <sub>FM</sub>	I <sub>F</sub> = 200 A	-	1.70	2.05	
		I <sub>F</sub> = 200 A, T <sub>J</sub> = 125 °C	-	1.50	1.78	
Reverse leakage current	I <sub>RM</sub>	V <sub>R</sub> = V <sub>R</sub> rated	-	0.1	50	μA
neverse leakage current		$T_J = 175 ^{\circ}\text{C},  V_R = V_R  \text{rated}$	-	0.30	2	mA
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 600 V	-	77	=	pF

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		$I_F = 1.0 \text{ A, } dI_F/dt = 1.0 \text{ A}$	$= 200 \text{ A/}\mu\text{s}, \text{ V}_{\text{R}} = 30 \text{ V}$	-	43	-	
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C	I <sub>F</sub> = 50 A dI <sub>F</sub> /dt = 200 A/μs V <sub>R</sub> = 200 V	-	83	-	ns - A - nC
		T <sub>J</sub> = 125 °C		-	182	-	
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 25 °C		-	7	-	
reak recovery current		T <sub>J</sub> = 125 °C		-	18	-	
Boyeres resovery charge	$Q_{rr}$	T <sub>J</sub> = 25 °C		-	290	=	
Reverse recovery charge		T <sub>J</sub> = 125 °C		-	1595	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Junction to case, single leg conducting	D		-	-	0.43	
Junction to case, both leg conducting	R <sub>thJC</sub>		-	-	0.215	°C/W
Case to heatsink	R <sub>thCS</sub>	Flat, greased surface	-	0.05	-	
Weight			-	30	-	g
Mounting toyage		Torque to terminal	-	-	1.1 (9.7)	Nm (lbf.in)
Mounting torque		Torque to heatsink	-	-	1.8 (15.9)	Nm (lbf.in)
Case style			SOT-227			







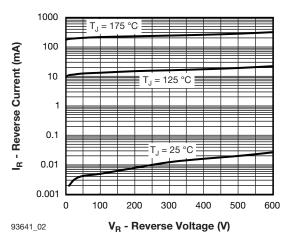


Fig. 2 - Typical Values of Reverse Current vs.Reverse Voltage

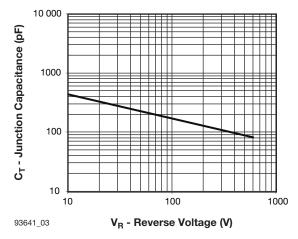


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

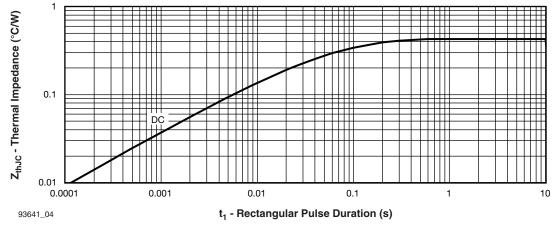


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics

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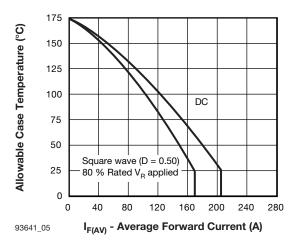


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

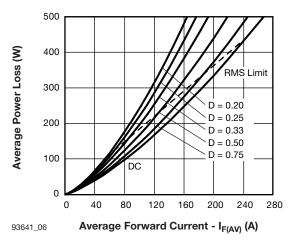


Fig. 6 - Forward Power Loss Characteristics

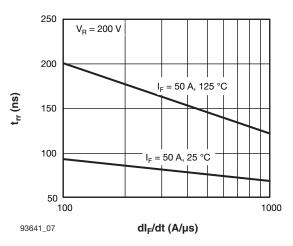


Fig. 7 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

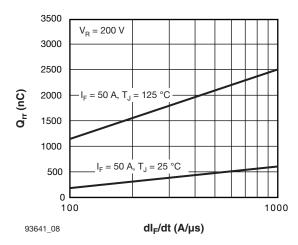


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt

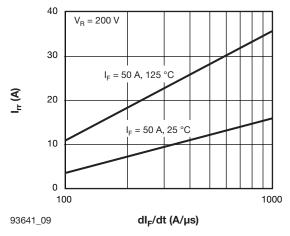


Fig. 9 - Typical I<sub>rr</sub> Diode vs. dI<sub>F</sub>/dt

#### Note

 $\begin{array}{ll} \text{(1)} & \text{Formula used: } T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}; \\ Pd = \text{forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 6)}; \\ Pd_{REV} = \text{inverse power loss} = V_{R1} \times I_R \text{ (1 - D)}; I_R \text{ at } V_{R1} = \text{rated } V_R \\ \end{array}$ 

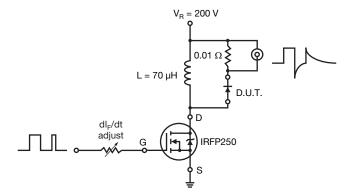
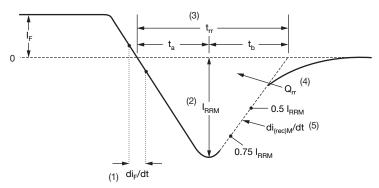


Fig. 10 - Reverse Recovery Parameter Test Circuit



- (1) di<sub>F</sub>/dt rate of change of current through zero crossing
- (2)  $I_{RRM}$  peak reverse recovery current
- (3)  $t_{rr}$  reverse recovery time measured from zero crossing point of negative going  $I_F$  to point where a line passing through 0.75  $I_{RRM}$  and 0.50  $I_{RRM}$  extrapolated to zero current.
- (4)  $\mathbf{Q}_{\rm rr}$  area under curve defined by  $\mathbf{t}_{\rm rr}$  and  $\mathbf{I}_{\rm RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

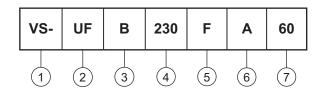
(5) di<sub>(rec)M</sub>/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 11 - Reverse Recovery Waveform and Definitions



#### **ORDERING INFORMATION TABLE**

Device code



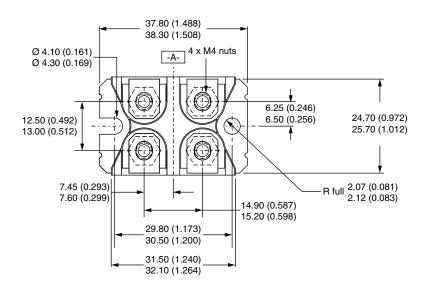
- Vishay Semiconductors product
- 2 Ultrafast rectifier
- 3 Ultrafast Pt diffused
- Current rating (230 = 230 A)
- 5 Circuit configuration (two separate diodes, parallel pin-out)
- 6 Package indicator (SOT-227 standard insulated base)
- 7 Voltage rating (60 = 600 V)

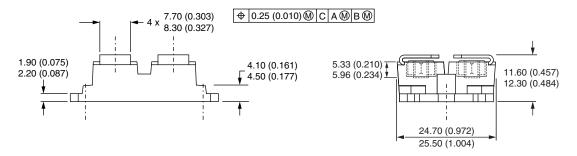
CIRCUIT CONFIGURATION						
CIRCUIT	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING				
Two separate diodes, parallel pin-out	F	Lead Assignment  4 0 0 3 4 1 0 0 2 1				

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95423				
Packaging information	www.vishay.com/doc?95425				

### SOT-227 Generation 2

### **DIMENSIONS** in millimeters (inches)





#### Note

· Controlling dimension: millimeter



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